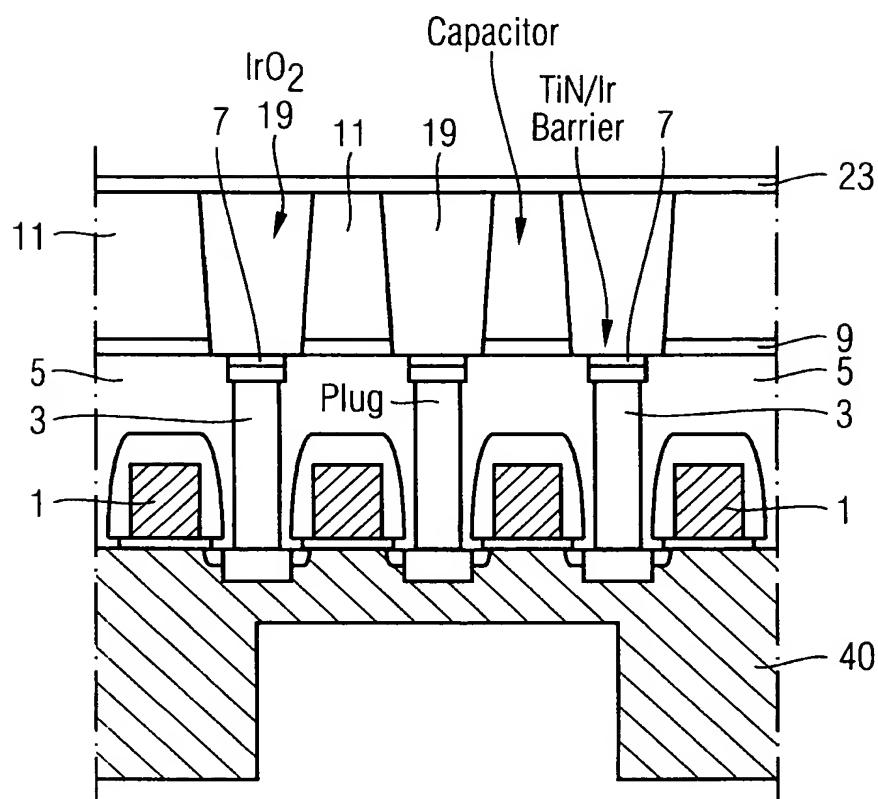




1/7

**FIG 1**  
Prior Art





Appn No.: 10/677,099

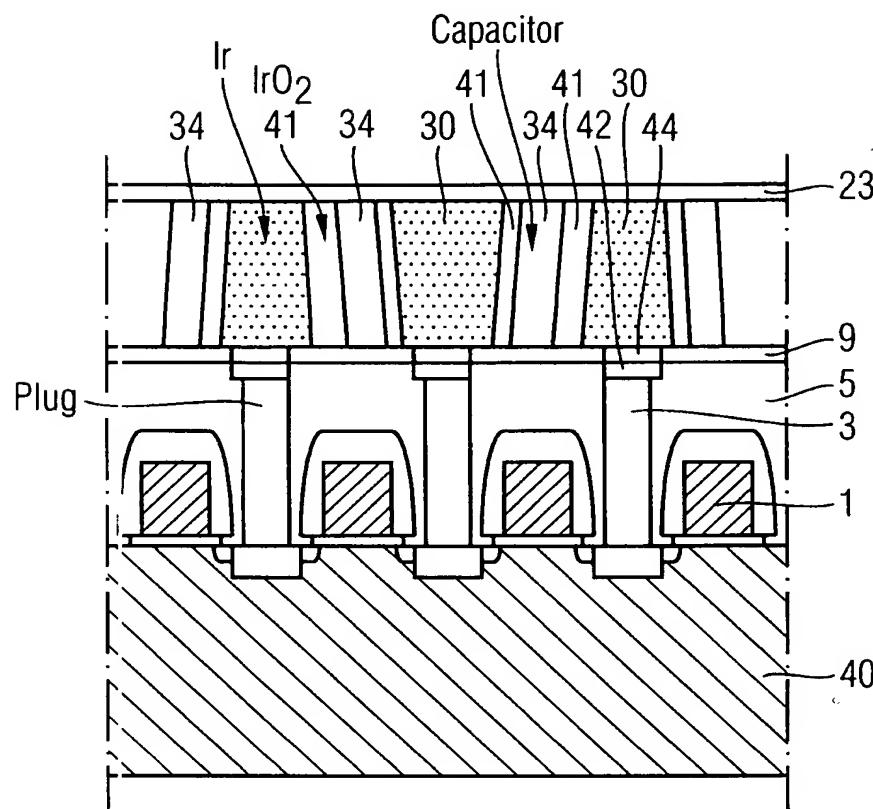
Applicant(s): Haoren Zhuang et al.

A DEVICE AND A METHOD FOR FORMING A CAPACITOR DEVICE

Page 2 of 7

2/7

FIG 2

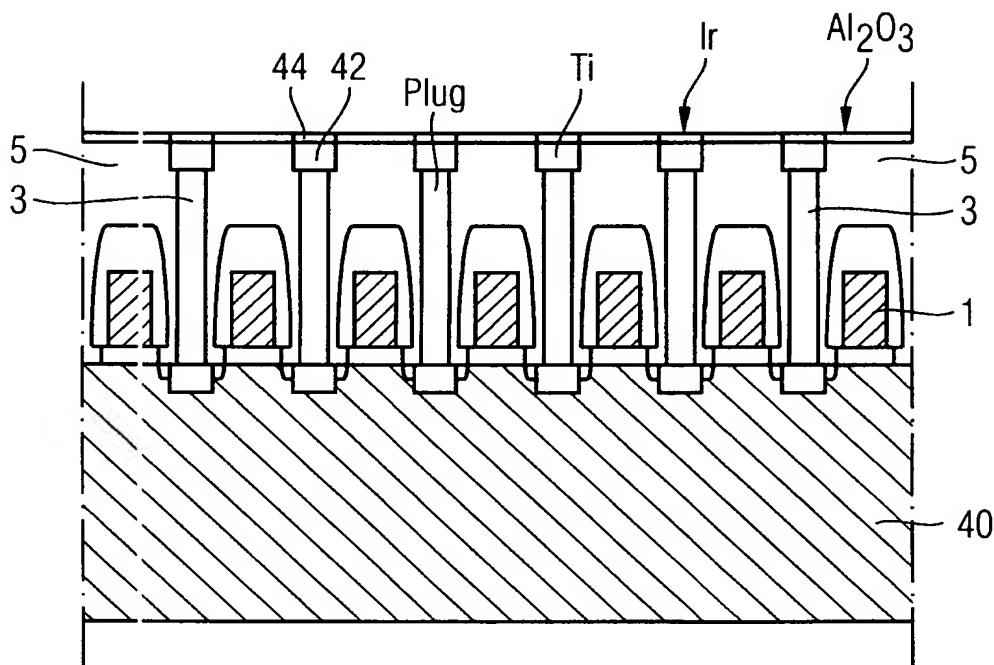




3/7

## FIG 3

Before Capacitor Process

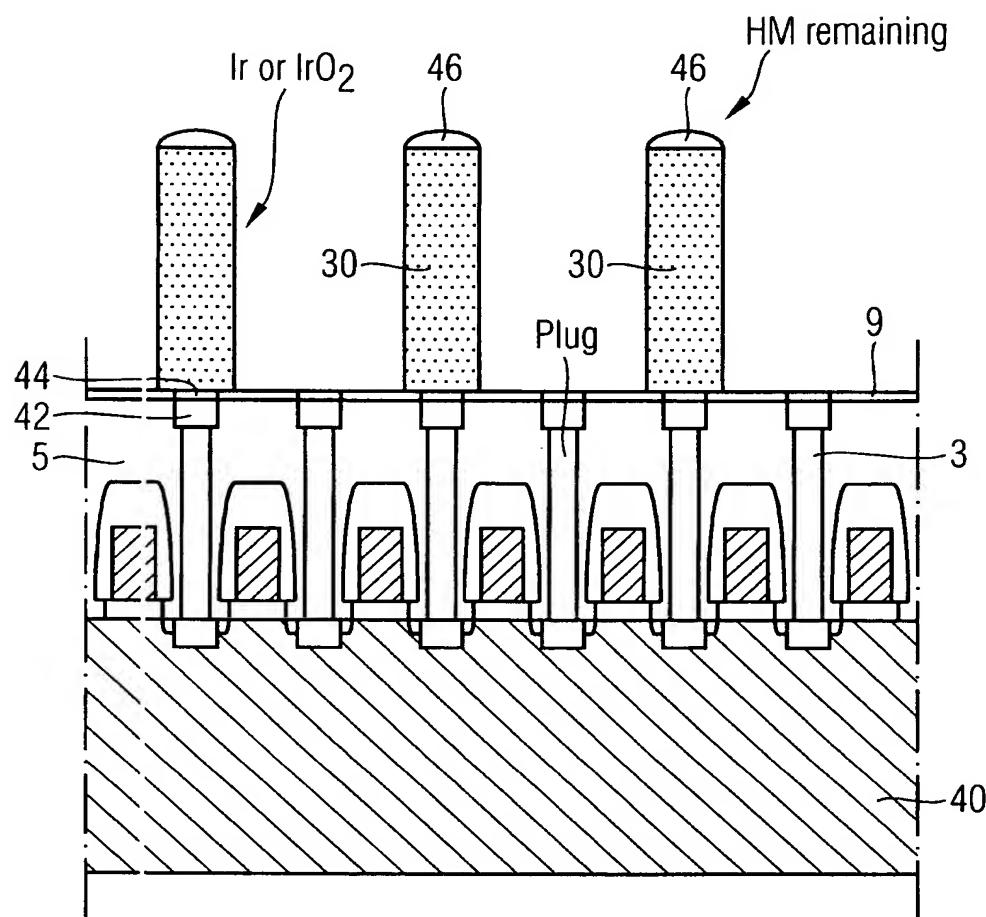




4/7

FIG 4

Ir or IrO<sub>2</sub> Deposit and RIE

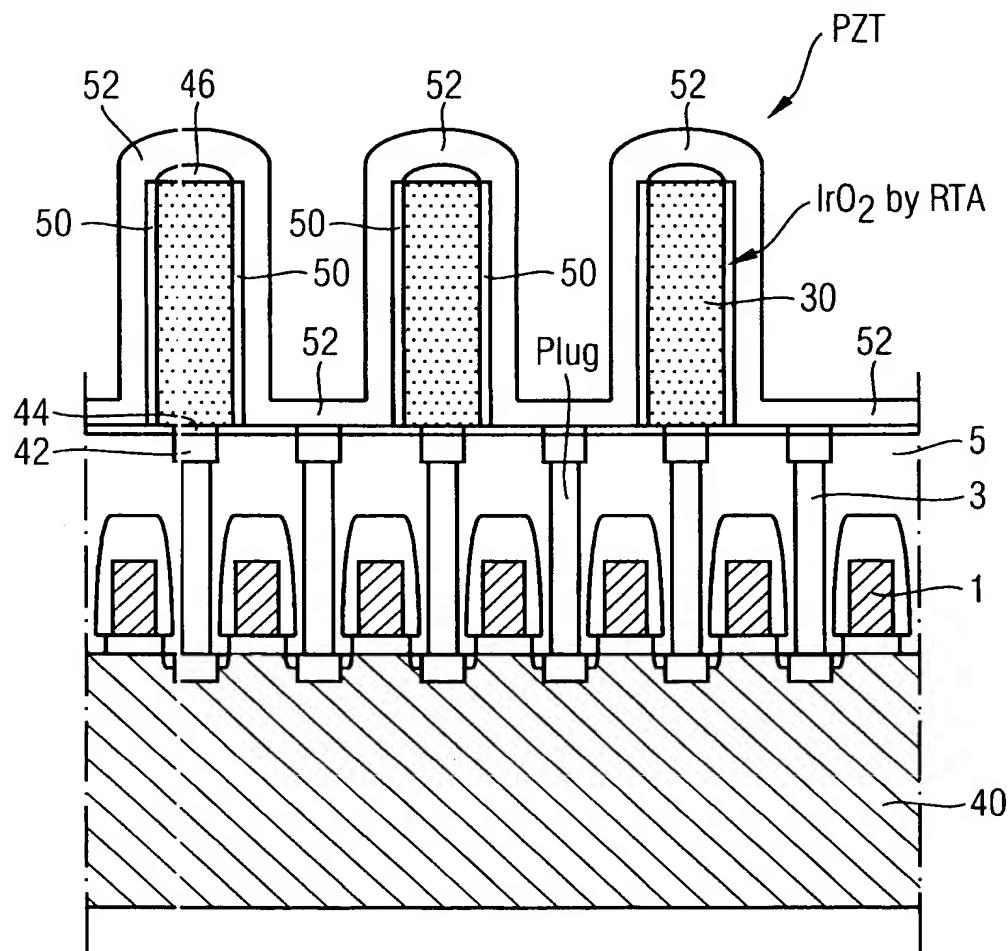




5/7

## FIG 5

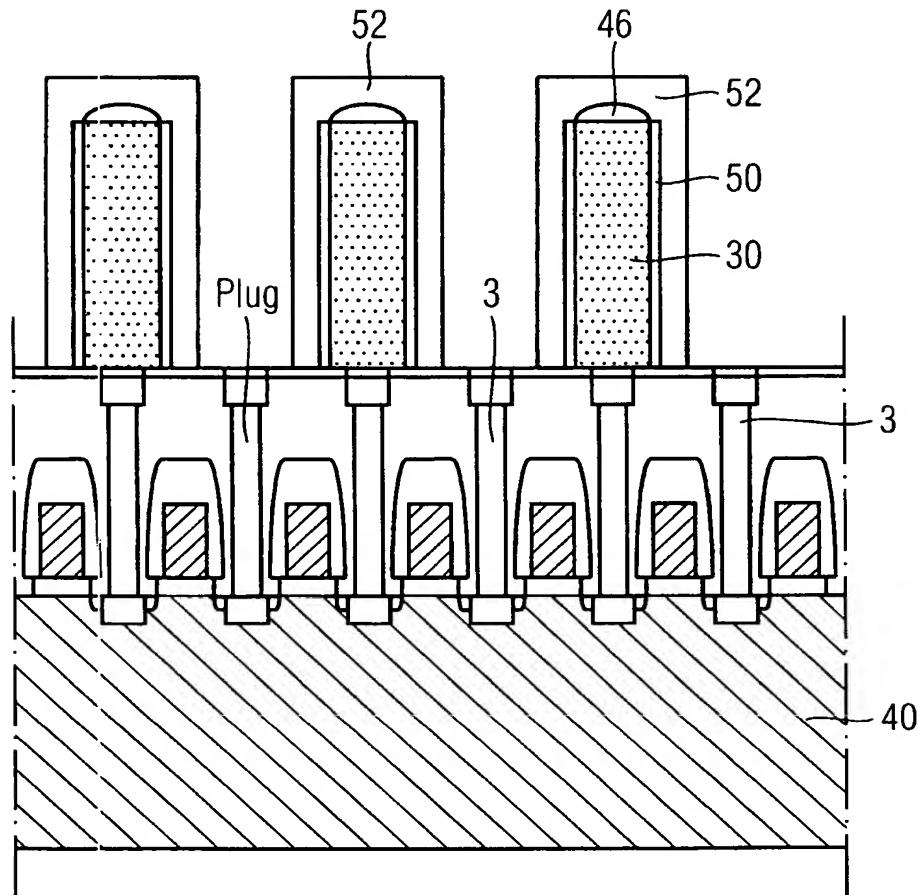
Making  $\text{IrO}_2$  on Ir surface  
(by RTA, if electrode is  $\text{IrO}_2$ , RTA is not necessary)  
and PZT Deposit on Surface





6/7

FIG 6  
PZT Etch Back





7/7

## FIG 7

Fill IrO<sub>2</sub> and Fill Ir  
(Or Only fill IrO<sub>2</sub>)  
CMP and then Al<sub>2</sub>O<sub>3</sub> deposit

